P-Channel Enhancement Mode MOSFET

Description

The IPD90P03P404ATMA1 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

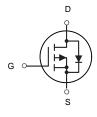


TO-252-2L

General Features

 $V_{DS} = -30V$ $I_{D} = -100A$

 $R_{DS(ON)}$ <4.5m Ω @ V_{GS} =-10V



P-Channel MOSFET

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD90P03P404ATMA1	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	-30	V
VGSS	Gate-Source Voltage	±20	V
ID	Continuous Drain Current T _C = 25℃	-100	А
ID	Continuous Drain Current T _C = 100 ℃	-59	А
IDM	Pulsed Drain Current note1	-360	А
EAS	Single Pulsed Avalanche Energy note2	210	mJ
PD	Power Dissipation T _C = 25°C	109	W
RθJC	Thermal Resistance, Junction to Case	1.4	°C/W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	$^{\circ}$

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Electrical Characteristics@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID= -250μA	-30	-33	-	V
IDSS	Zero Gate Voltage Drain Current	VDS= -30V, VGS=0V,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	VDS=0V, VGS= ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID= -250μA	-1.0	-1.6	-2.5	V
DD0()	Static Drain-Source on-Resistance	VGS= -10V, ID= -30A	-	3.5	4.5	
RDS(on)		VGS= -4.5V, ID= -20A	-	4.8	6.2	mΩ
Ciss	Input Capacitance	VDS= -15V, VGS=0V,	-	6800	-	pF
Coss	Output Capacitance	f=1.0MHz	-	769	-	pF
Crss	Reverse Transfer Capacitance		-	726	-	pF
Qg	Total Gate Charge	VDS= -15V, ID= -30A,	-	30	-	nC
Qgs	Gate-Source Charge	VGS= -10V	-	6	-	nC
Qgd	Gate-Drain("Miller") Charge		-	8	-	nC
td(on)	Turn-on Delay Time		-	11	-	ns
tr	Turn-on Rise Time	VDD= -15V, ID= -30A,	-	13	-	ns
td(off)	Turn-off Delay Time	VGS= -10V, RGEN=2.5Ω	-	52	-	ns
tf	Turn-off Fall Time		-	21	-	ns
IS	Maximum Continuous Drain to Source	DiodeForward Current	-	-	-100	Α
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-360	Α
VSD	Drain to Source Diode Forward Voltage	VGS=0V, IS= -30 A		-0.8	-1.2	V

Notes:

- 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 2 \ E AS condition: T J = 25 °C, V DD = -15 V, V G = -10 V, R G = 25 Ω , L=0.5 mH, I AS = -29 A
- 3、Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%



Typical Characteristics

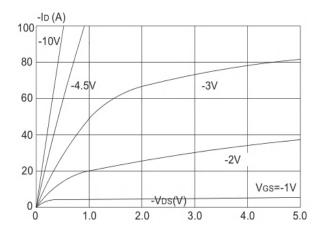


Figure1: Output Characteristics

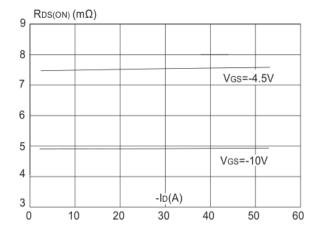


Figure 3:On-resistance vs. Drain Current

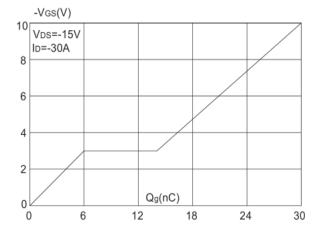


Figure 5: Gate Charge Characteristics

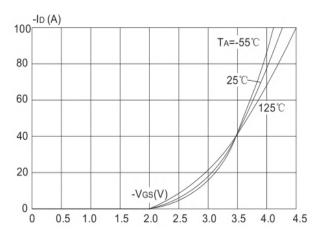


Figure 2: Typical Transfer Characteristics

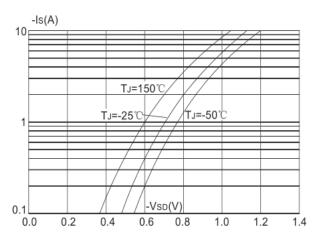


Figure 4: Body Diode Characteristics

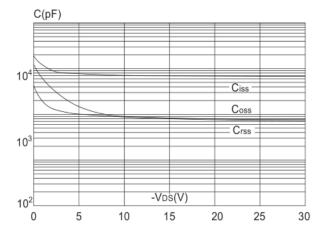


Figure 6: Capacitance Characteristics

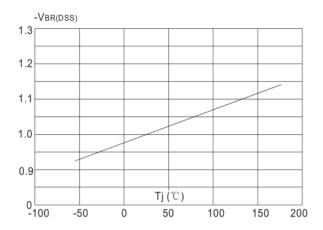


Figure 7: Normalized Breakdown Voltage vs.

Junction Temperature

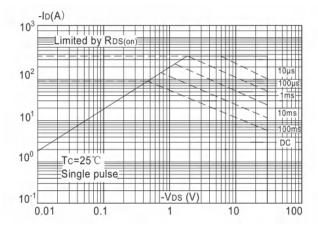


Figure 9: Maximum Safe Operating Area

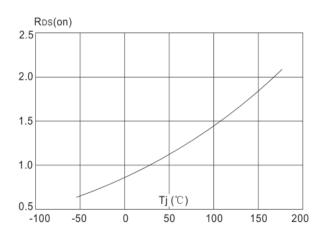


Figure 8: Normalized on Resistance vs.

Junction Temperature

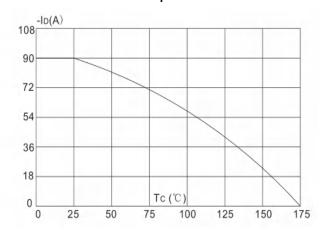


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

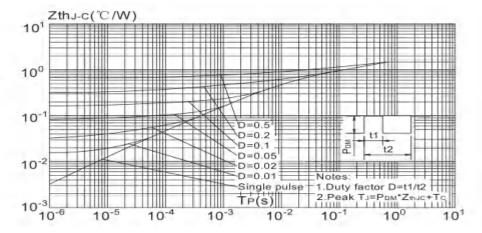
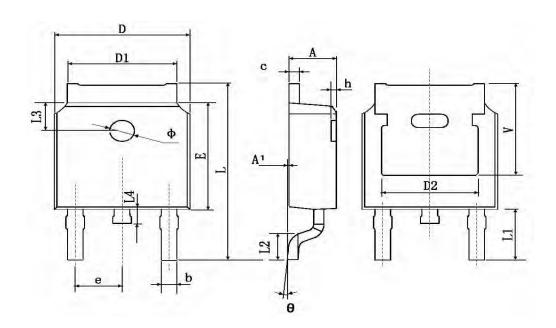


Figure.11: Maximum Effective

Transient Thermal Impedance, Junction-to-Case



TO-252-2L Package Information



Dimensions In Millimeters		Dimensions In Inches		
Min.	Max.	Min.	Max.	
2.200	2.400	0.087	0.094	
0.000	0.127	0.000	0.005	
0.660	0.860	0.026	0.034	
0.460	0.580	0.018	0.023	
6.500	6.700	0.256	0.264	
5.100	5.460	0.201	0.215	
4.830 TYP.		0.190 TYP.		
6.000	6.200	0.236	0.244	
2.186	2.386	0.086	0.094	
9.800	10.400	0.386	0.409	
2.900 TYP.		0.114 TYP.		
1.400	1.700	0.055	0.067	
	1.600 TYP.		0.063 TYP.	
0.600	1.000	0.024	0.039	
1.100	1.300	0.043	0.051	
0°	8°	0°	8°	
0.000	0.300	0.000	0.012	
5.350 TYP.		0.211 TYP.		
	Min. 2.200 0.000 0.660 0.460 6.500 5.100 4.830 6.000 2.186 9.800 2.900 1.400 1.600 0.600 1.100 0° 0.000	Min. Max. 2.200 2.400 0.000 0.127 0.660 0.860 0.460 0.580 6.500 6.700 5.100 5.460 4.830 TYP. 6.200 2.186 2.386 9.800 10.400 2.900 TYP. 1.700 1.600 TYP. 0.600 1.100 1.300 0° 8° 0.000 0.300	Min. Max. Min. 2.200 2.400 0.087 0.000 0.127 0.000 0.660 0.860 0.026 0.460 0.580 0.018 6.500 6.700 0.256 5.100 5.460 0.201 4.830 TYP. 0.190 6.000 6.200 0.236 2.186 2.386 0.086 9.800 10.400 0.386 2.900 TYP. 0.114 1.400 1.700 0.055 1.600 TYP. 0.063 0.600 1.000 0.024 1.100 1.300 0.043 0° 8° 0° 0.000 0.300 0.000	

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